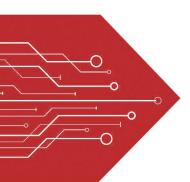
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet





1. OUT

2. IN

SOT-23 3. GND

FEATURE

Maximum Output Current $I_{O:}$ 0.1 A Output Voltage $V_{O:}$ 5 V Continuous Total Dissipation $P_{D:}$ 0.25 W (T_{a} = 25 °C)

MARKING: L05

ABSOLUTE MAXIMUM RATINGS (Operating temperature range applies unless otherwise specified)

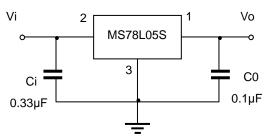
Parameter	Symbol	Value	Unit
Input Voltage	Vi	30	V
Thermal Resistance from Junction to Ambient	R _{θJA}	160	°C/W
Operating Junction Temperature Range	T _{OPR}	-40~+125	°C
Storage Temperature Range	T _{STG}	-65~+150	$^{\circ}$

ELECTRICAL CHARACTERISTICS AT SPECIFIED VIRTUAL JUNCTION TEMPERATURE (Vi=10V,Io=40mA,Ci=0.33uF,,Co=0.1uF, unless otherwise specified)

Parameter	Symbol	Test conditions		Тур	Max	Unit
Output voltage	Vo	T _J =25°C 3% 2%	4.85	5.0	5.15	V
			4.90	5.0	5.10	V
		7V≤Vi≤20V, Io=1mA~40mA	4.75	5.0	5.25	V
		Io=1mA~70mA	4.75	5.0	5.25	V
Load Regulation	ΔVο	lo=1mA~100mA,T _J =25 °C		15	60	mV
Load Regulation	Δνο	Io=1mA~40mA,T _J =25°C		8	30	mV
Lie a secondation	۸۱/۵	7V≤Vi _I ≤20V		32	150	mV
Line regulation	ΔVο	8V≤Vi≤20V,T _J =25 °C		26	100	mV
Quiescent Current	Iq	T _J =25℃		3.8	6	mA
Quiacoant Current Change	Δlq	8V≤Vi≤20V			1.5	mA
Quiescent Current Change	Δlq	1mA≤V _I ≤40mA			0.1	mA
Output Noise Voltage	V _N	10Hz≤f≤100KHz,T _J =25 ℃		42		μV/Vo
Ripple Rejection	RR	8V≤Vi≤20V,f=120Hz	41	49		dB
Dropout Voltage	Vd	T _J =25℃		1.7		V

^{*} Pulse test.

TYPICAL APPLICATION

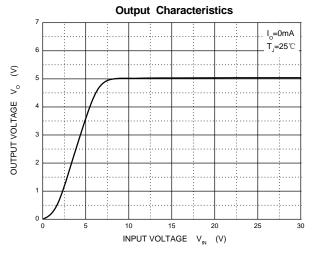


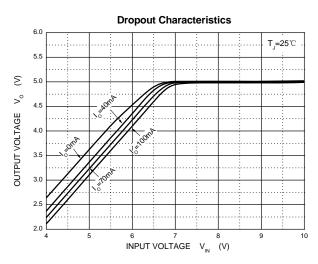
Note: Bypass capacitors are recommended for optimum stability and transient response and should be located as close as Possible to the regulators.

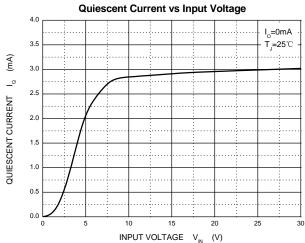


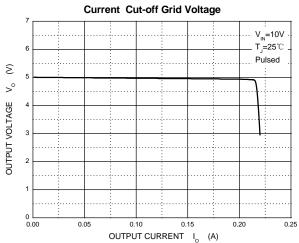
MS78L05S HF

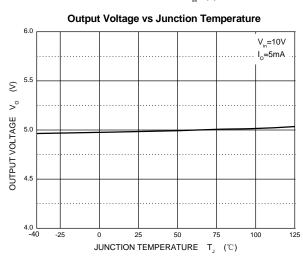


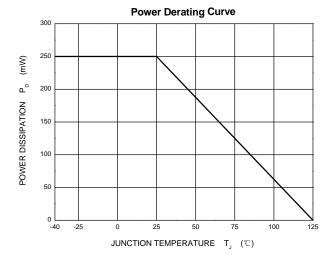








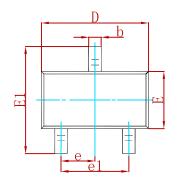


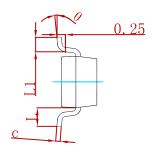


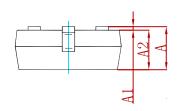


Semiconductor Compiance

PACKAGE MECHANICAL DATA

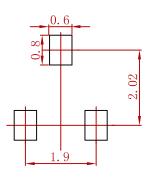






Cumhal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MS78L05S	SOT-23	3000



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